



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-02L Plastic-Encapsulate Diodes

FRB751 Schottky barrier Diodes

DESCRIPTION

Silicon epitaxial planar

FEATURES

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

APPLICATION

High speed switching For Detection

For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

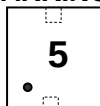
WBFBP-02L

(0.8×0.6×2L)



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MARKING: 5



Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	30	mA
Peak forward surge current	I _{FSM}	150	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~125	°C

Electrical Ratings @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F			0.37	V	I _F =1mA
Reverse current	I _R			0.5	μ A	V _R =30V
Capacitance between terminals	C _T		2		pF	V _R =1V,f=1MHZ

Typical Characteristics

●Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

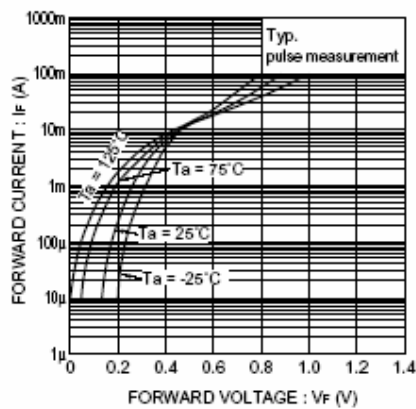


Fig. 1 Forward characteristics

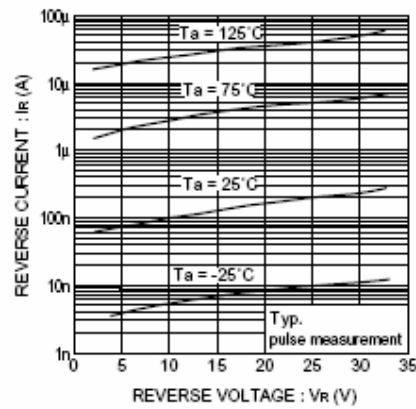


Fig. 2 Reverse characteristics

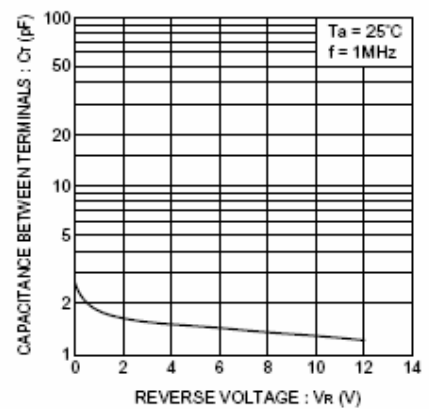


Fig. 3 Capacitance between terminals characteristics